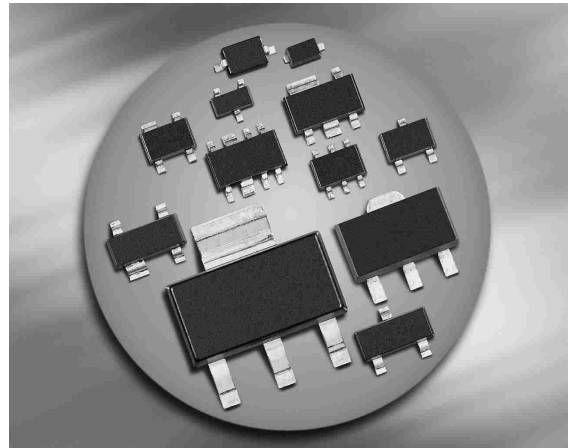
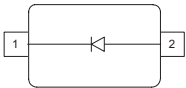


Silicon Tuning Diode

- Excellent linearity
- Low series resistance
- Designed for low tuning voltage operation for VCO's in mobile communications equipment
- Very low capacitance spread



BBY56-02W
BBY56-03W



Type	Package	Configuration	L_S (nH)	Marking
BBY56-02W	SCD80	single	0.6	66
BBY56-03W	SOD323	single	1.8	6 red

Maximum Ratings at $T_A = 25^\circ\text{C}$, unless otherwise specified

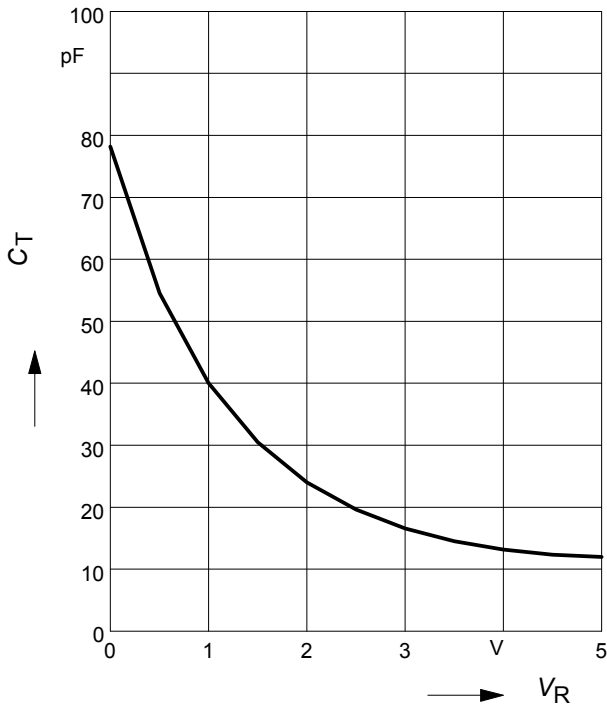
Parameter	Symbol	Value	Unit
Diode reverse voltage	V_R	10	V
Forward current	I_F	20	mA
Operating temperature range	T_{op}	-55 ... 150	°C
Storage temperature	T_{stg}	-55 ... 150	

Electrical Characteristics at $T_A = 25^\circ\text{C}$, unless otherwise specified

Parameter	Symbol	Values			Unit
		min.	typ.	max.	
DC Characteristics					
Reverse current	I_R				nA
$V_R = 6\text{ V}$		-	-	5	
$V_R = 6\text{ V}, T_A = 85^\circ\text{C}$		-	-	100	
AC Characteristics					
Diode capacitance	C_T				pF
$V_R = 1\text{ V}, f = 1\text{ MHz}$		37	40	43	
$V_R = 2\text{ V}, f = 1\text{ MHz}$		22	-	25	
$V_R = 3\text{ V}, f = 1\text{ MHz}$		14.8	15.8	16.8	
$V_R = 4\text{ V}, f = 1\text{ MHz}$		-	12.1	-	
Capacitance ratio	C_{T1}/C_{T3}				
$V_R = 1\text{ V}, V_R = 3\text{ V}, f = 1\text{ MHz}$		2.15	2.53	-	
$V_R = 1\text{ V}, V_R = 4\text{ V}, f = 1\text{ MHz}$		-	3.3	-	
Series resistance	r_S				Ω
$V_R = 1\text{ V}, f = 470\text{ MHz}$		-	0.25	-	

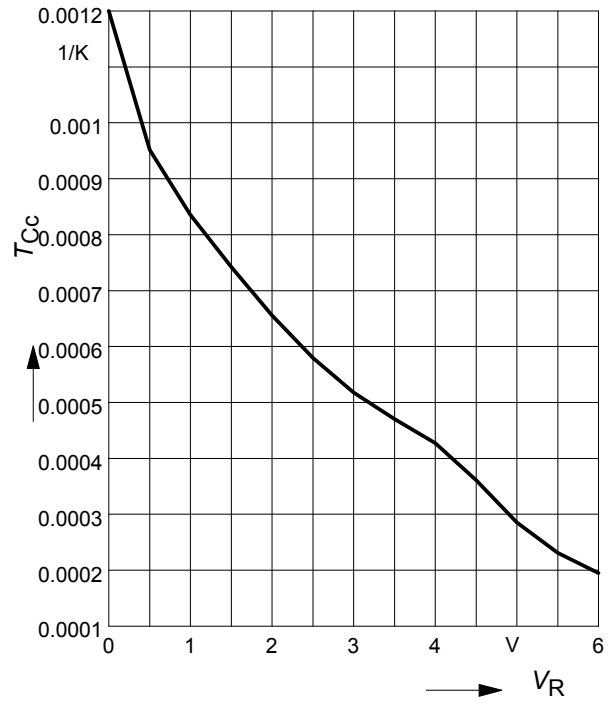
Diode capacitance $C_T = f(V_R)$

$f = 1\text{MHz}$



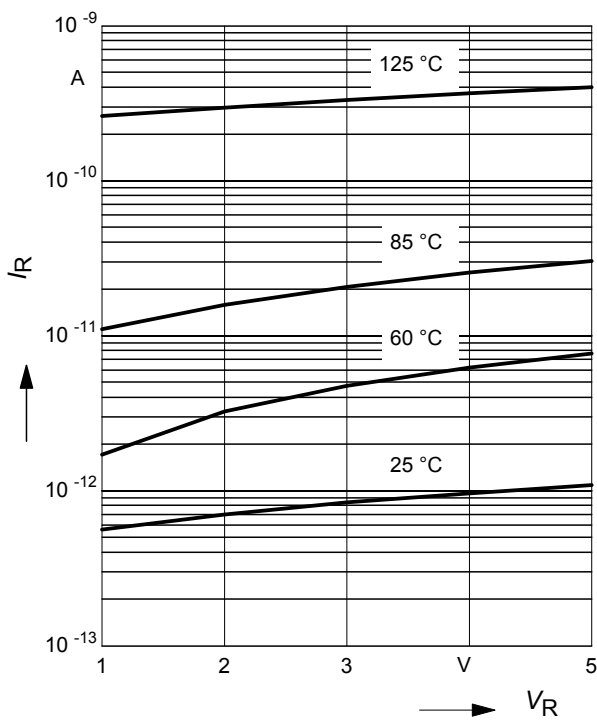
Temperature coefficient of the diode capacitance $T_{Cc} = f(V_R)$

$f = 1\text{MHz}$



Reverse current $I_R = f(V_R)$

$T_A = \text{Parameter}$





LittleDiode supplies new, hard to find or obsolete electronic components and semiconductors all over the world.

With over two million different components listed you are sure to find the part you need.

Feel free to visit us today at our online store:

LittleDiode.com

Looking forward to providing you with the best possible service.